

## 100V N-Channel Trench Power MOSFET

### Product Summary

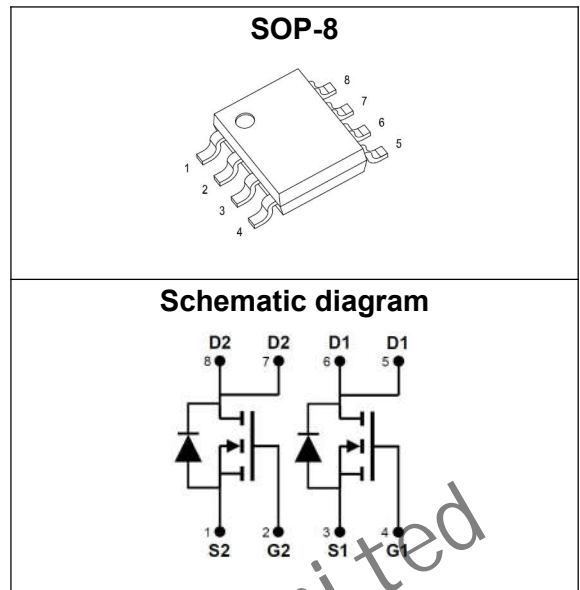
$V_{(BR)DSS}$	$R_{DS(on)TYP}$	$I_D$
100V	80mΩ@10V	12A

### Features

- Very Low On-resistance  $R_{DS(on)}$
- Low  $C_{rss}$
- Fast switching
- Improved dv/dt capability

### Applications

- DC/DC Converter
- Load Switch for Portable Devices
- Battery Switch



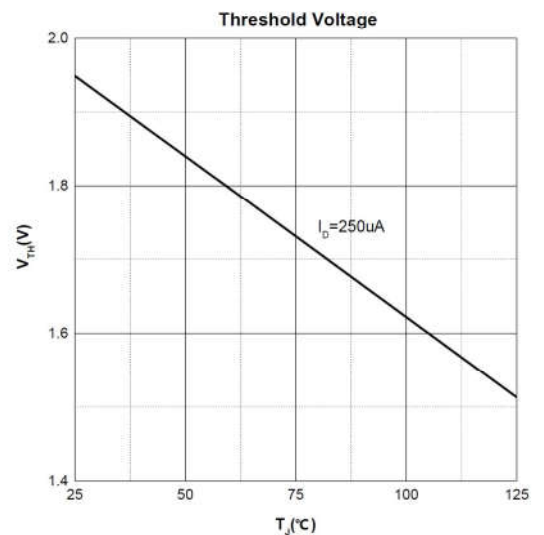
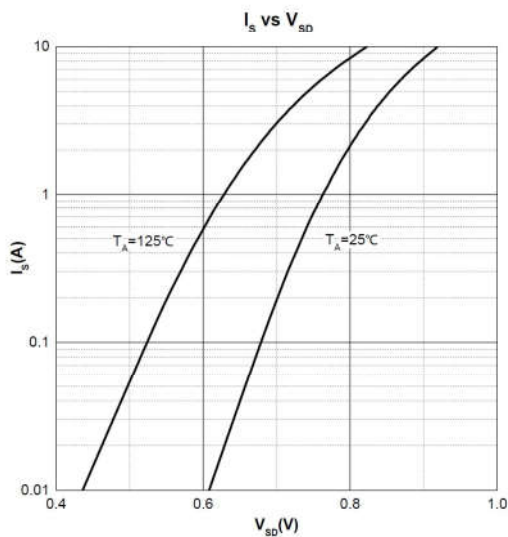
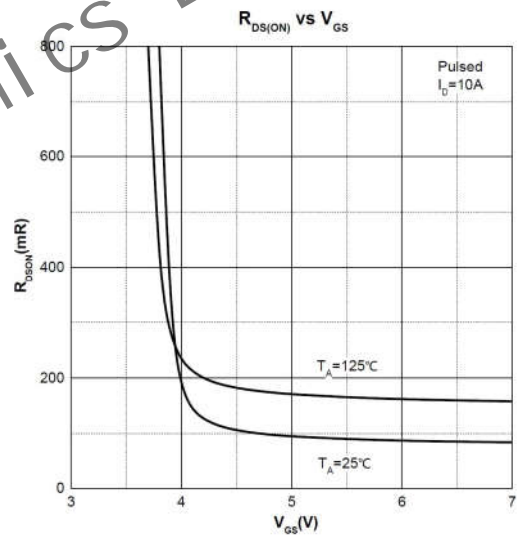
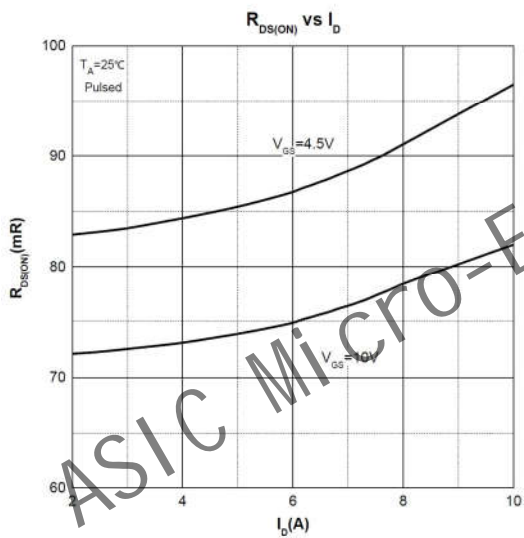
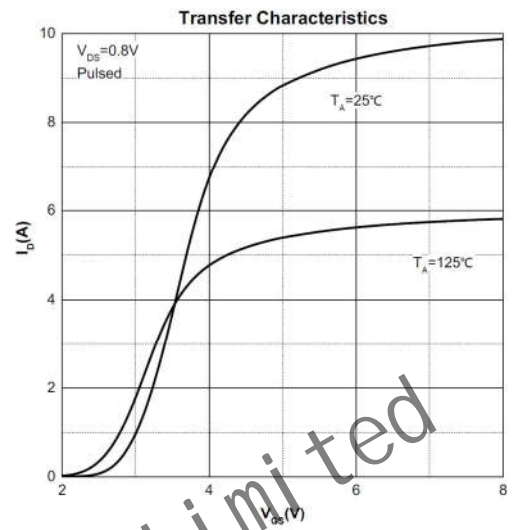
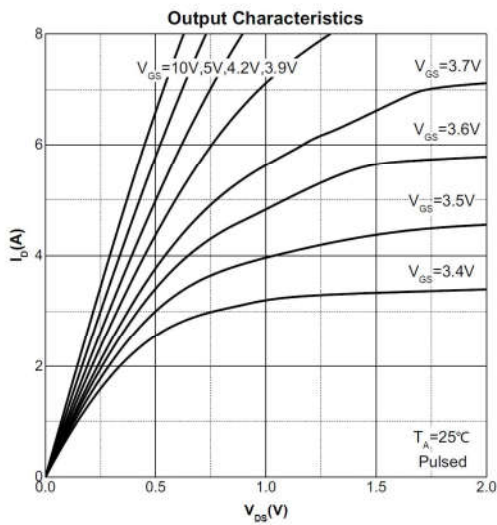
### Absolute Maximum rating ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Units
Drain-Source Voltage	$V_{DS}$	100	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Drain Current	$I_D$	12	A
Drain Current - Pulsed	$I_{DM}$	35	A
Power Dissipation	$P_D$	1.5	W
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	85	$^\circ\text{C/W}$
Operating and Storage Temperature Range	$T_J, T_{STG}$	-55 to +150	$^\circ\text{C}$

**Electrical Characteristics (T<sub>A</sub> = 25°C unless otherwise noted)**

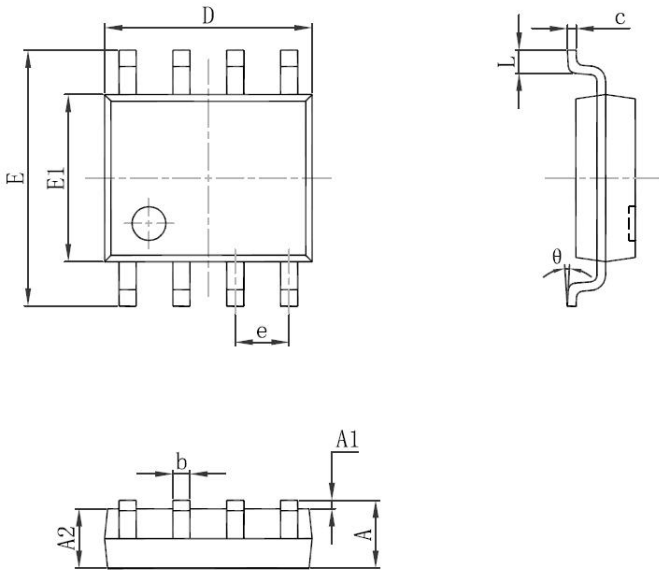
Parameter	Symbol	Test Condition	Min	Type	Max	Unit
<b>Static Characteristics</b>						
Drain - Source Breakdown Voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA	100			V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 100V, V <sub>GS</sub> = 0V			1	μA
Gate - Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V			±100	nA
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA	1	2	3	V
Drain-source On-resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10V, I <sub>D</sub> = 4A		80	100	mΩ
<b>Dynamic Characteristics</b>						
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> = 50V, V <sub>GS</sub> = 0V, f= 1MHz		847		pF
Output Capacitance	C <sub>oss</sub>			33		
Reverse Transfer Capacitance	C <sub>rss</sub>			29		
<b>Switching Characteristics</b>						
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> = 50V, V <sub>GS</sub> = 10V, I <sub>D</sub> = 10A		20		nC
Gate-source Charge	Q <sub>gs</sub>			1.8		
Gate-drain Charge	Q <sub>gd</sub>			4		
Turn-on Delay Time	t <sub>d(on)</sub>	V <sub>GS</sub> = 10V, V <sub>DS</sub> = 50V, R <sub>L</sub> = 15Ω R <sub>GEN</sub> = 2.5Ω		11		ns
Turn-on Rise Time	t <sub>r</sub>			7		
Turn-off Delay Time	t <sub>d(off)</sub>			34		
Turn-off Fall Time	t <sub>f</sub>			9		
<b>Source - Drain Diode Characteristics</b>						
Diode Forward Voltage	V <sub>SD</sub>	V <sub>GS</sub> = 0V, I <sub>S</sub> = 10A			1.2	V

## Typical Characteristic



## Dimension

### SOP8



Symbol	Dimensions		Dimensions	
	Min	Max	Min	Max
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.007	0.010
D	4.800	5.000	0.189	0.197
e	1.270 (BSC)		0.050 (BSC)	
E	5.800	6.200	0.228	0.244
E1	3.800	4.000	0.150	0.157
L	0.400	1.270	0.016	0.050
$\theta$	0°	S°	0°	8°

ASIC Micro-Electronics Limited